

L2	35	l1 and (third near2 region) and (fourth near2 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:18
L3	27	l1 and (third near2 region) and (fourth near2 region).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:18
L4	27	l1 and (third near2 region).clm. and (fourth near2 region).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:19
L5	26	l1 and (third near2 region).clm. and (fourth near2 region).clm. and surface.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:23
L6	18	l1 and (third near2 region).clm. and (fourth near2 region).clm. and surface.clm. and (control adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:19
L7	15	l1 and (third near2 region).clm. and (fourth near2 region).clm. and surface.clm. and (control adj electrode).clm. and junction.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:19
L8	24	l1 and (third near2 region).clm. near10 surface.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:24
L9	12	l1 and (third near2 region).clm. near10 surface.clm. and (semiconductor adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 11:25